# D44VH10 (NPN), D45VH10 (PNP)

# **Complementary Silicon Power Transistors**

These complementary silicon power transistors are designed for high-speed switching applications, such as switching regulators and high frequency inverters. The devices are also well-suited for drivers for high power switching circuits.

# **Features**

- Fast Switching
- Key Parameters Specified @ 100°C
- Low Collector-Emitter Saturation Voltage
- Complementary Pairs Simplify Circuit Designs
- These Devices are Pb-Free and are RoHS Compliant\*

# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	80	Vdc
Collector–Emitter Voltage	V <sub>CEV</sub>	100	Vdc
Emitter Base Voltage	V <sub>EB</sub>	7.0	Vdc
Collector Current – Continuous	Ic	15	Adc
Collector Current – Peak (Note 1)	I <sub>CM</sub>	20	Adc
Total Power Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	83 0.67	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Width  $\leq$  6.0 ms, Duty Cycle  $\leq$  50%.

# THERMAL CHARACTERISTICS

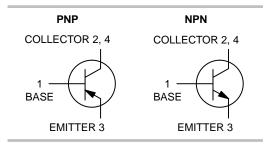
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T <sub>L</sub>	275	°C



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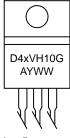
# 15 A COMPLEMENTARY SILICON POWER TRANSISTORS 80 V, 83 W





TO-220 CASE 221A STYLE 1

## **MARKING DIAGRAM**



x = 4 or 5

A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

# ORDERING INFORMATION

Device	Package	Shipping
D44VH10G	TO-220 (Pb-Free)	50 Units/Rail
D45VH10G	TO-220 (Pb-Free)	50 Units/Rail

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# D44VH10 (NPN), D45VH10 (PNP)

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 25 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	80	-	-	Vdc
Collector–Emitter Cutoff Current $(V_{CE} = Rated \ V_{CEV}, \ V_{BE(off)} = 4.0 \ Vdc)$ $(V_{CE} = Rated \ V_{CEV}, \ V_{BE(off)} = 4.0 \ Vdc, \ T_{C} = 100^{\circ}C)$		- -	- -	10 100	μAdc
Emitter Base Cutoff Current (V <sub>EB</sub> = 7.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	_	10	μAdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain ( $I_C = 2.0$ Adc, $V_{CE} = 1.0$ Vdc) ( $I_C = 4.0$ Adc, $V_{CE} = 1.0$ Vdc)	h <sub>FE</sub>	35 20	_ _	_ _	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc) D44VH10	V <sub>CE(sat)</sub>	_	_	0.4	Vdc
$(I_C = 8.0 \text{ Adc}, I_B = 0.8 \text{ Adc})$ D45VH10 $(I_C = 15 \text{ Adc}, I_B = 3.0 \text{ Adc}, T_C = 100^{\circ}\text{C})$		-	_	1.0	
D44VH10 D45VH10		- -	_ _	0.8 1.5	
Base–Emitter Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc)	V <sub>BE(sat)</sub>			4.0	Vdc
D44VH10 ( $I_C = 8.0 \text{ Adc}, I_B = 0.8 \text{ Adc}$ ) D45VH10		_	_	1.2	
(I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc, T <sub>C</sub> = 100°C) D44VH10 (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 Adc, T <sub>C</sub> = 100°C)		-	-	1.1	
D45VH10		-	_	1.5	
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth Product $(I_C = 0.1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 20 \text{ MHz})$	f <sub>T</sub>	_	50	-	MHz
Output Capacitance ( $V_{CB} = 10 \text{ Vdc}$ , $I_{C} = 0$ , $f_{test} = 1.0 \text{ MHz}$ )	C <sub>ob</sub>				pF
D44VH10 D45VH10		- -	120 275	-	
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	-		50	ns
Rise Time	t <sub>r</sub>	_	_	250	
Storage Time $(V_{CC} = 20 \text{ Vdc}, I_C = 8.0 \text{ Adc}, I_{B1} = I_{B2} = 0.8 \text{ Adc})$	t <sub>s</sub>	-	_	700	]
Fall Time	t <sub>f</sub>	-	-	90	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2%.

# D44VH10 (NPN), D45VH10 (PNP)

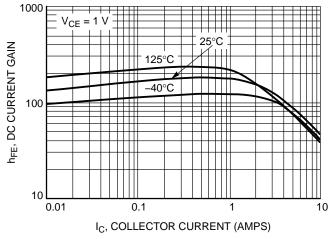


Figure 1. D44VH10 DC Current Gain

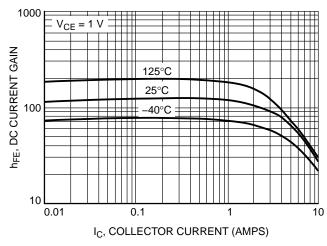


Figure 2. D45VH10 DC Current Gain

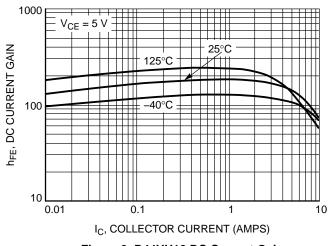


Figure 3. D44VH10 DC Current Gain

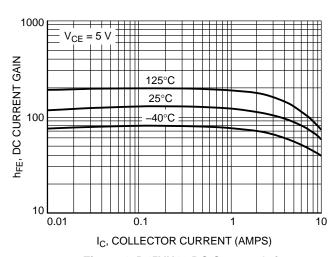


Figure 4. D45VH10 DC Current Gain

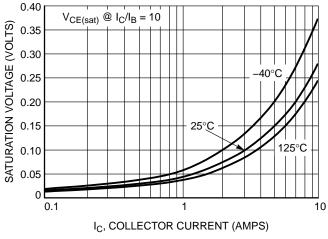


Figure 5. D44VH10 ON-Voltage

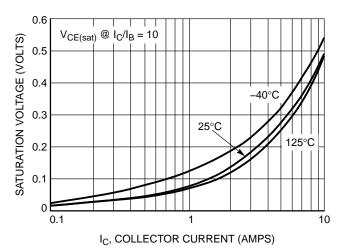


Figure 6. D45VH10 ON-Voltage

# D44VH10 (NPN), D45VH10 (PNP)

1.4

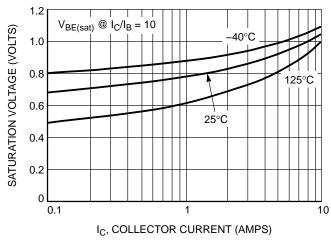
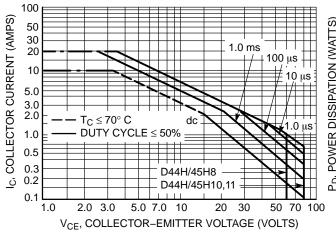


Figure 7. D44VH10 ON-Voltage

Figure 8. D45VH10 ON-Voltage



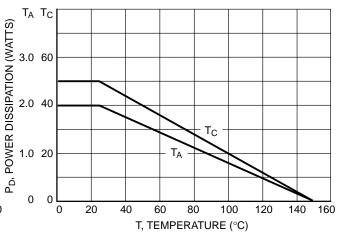


Figure 9. Maximum Rated Forward Bias Safe Operating Area

Figure 10. Power Derating

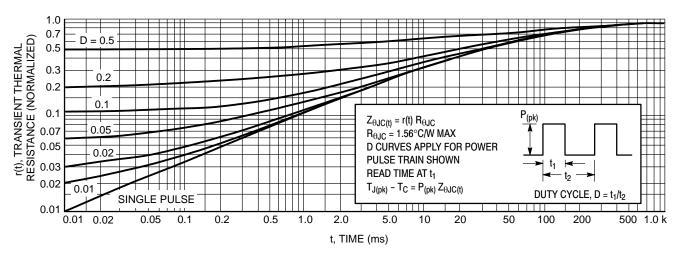
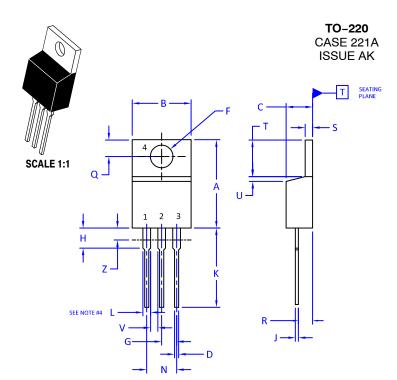


Figure 11. Thermal Response





**DATE 13 JAN 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN SOURCE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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